

Silicon PNP Power Transistors

2SA1695

DESCRIPTION

- With TO-3PN package
- Complement to type 2SC4468

APPLICATIONS

- Audio and general purpose

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

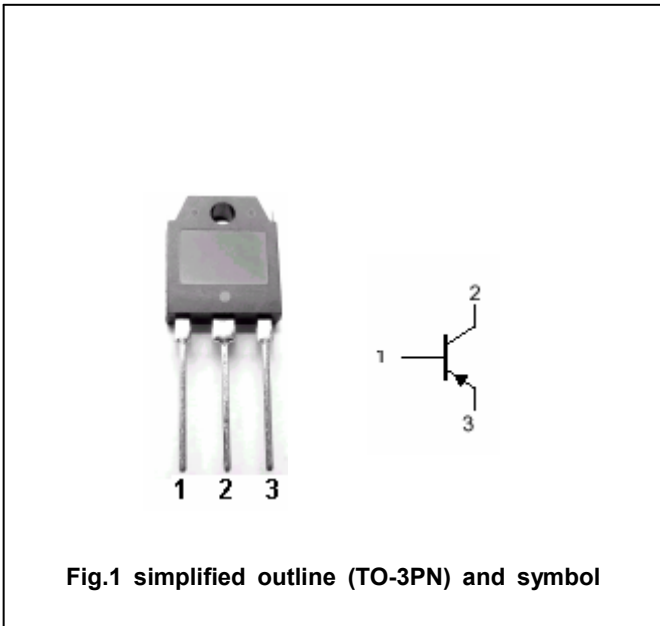


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-140	V
V _{CEO}	Collector-emitter voltage	Open base	-140	V
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current		-10	A
I _B	Base current		-4	A
P _C	Collector power dissipation	T _C =25□	100	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-50mA; I_B=0$	-140			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-5A; I_B=-0.5A$			-0.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-140V; I_E=0$			-10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-6V; I_C=0$			-10	μA
h_{FE}	DC current gain	$I_C=-3A; V_{CE}=-4V$	50		180	
C_{OB}	Output capacitance	$I_E=0; V_{CB}=-10V, f=1MHz$		400		pF
f_T	Transition frequency	$I_C=-0.5A; V_{CE}=-12V$		20		MHz

Switching times

t_{on}	Turn-on time	$I_C=-5A; R_L=12\Omega$ $I_{B1}=-I_{B2}=-0.5A$ $V_{CC}=-60V$		0.17		μs
t_s	Storage time			1.86		μs
t_f	Fall time			0.27		μs

◆ h_{FE} Classifications

O	P	Y
50-100	70-140	90-180

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PACKAGE OUTLINE

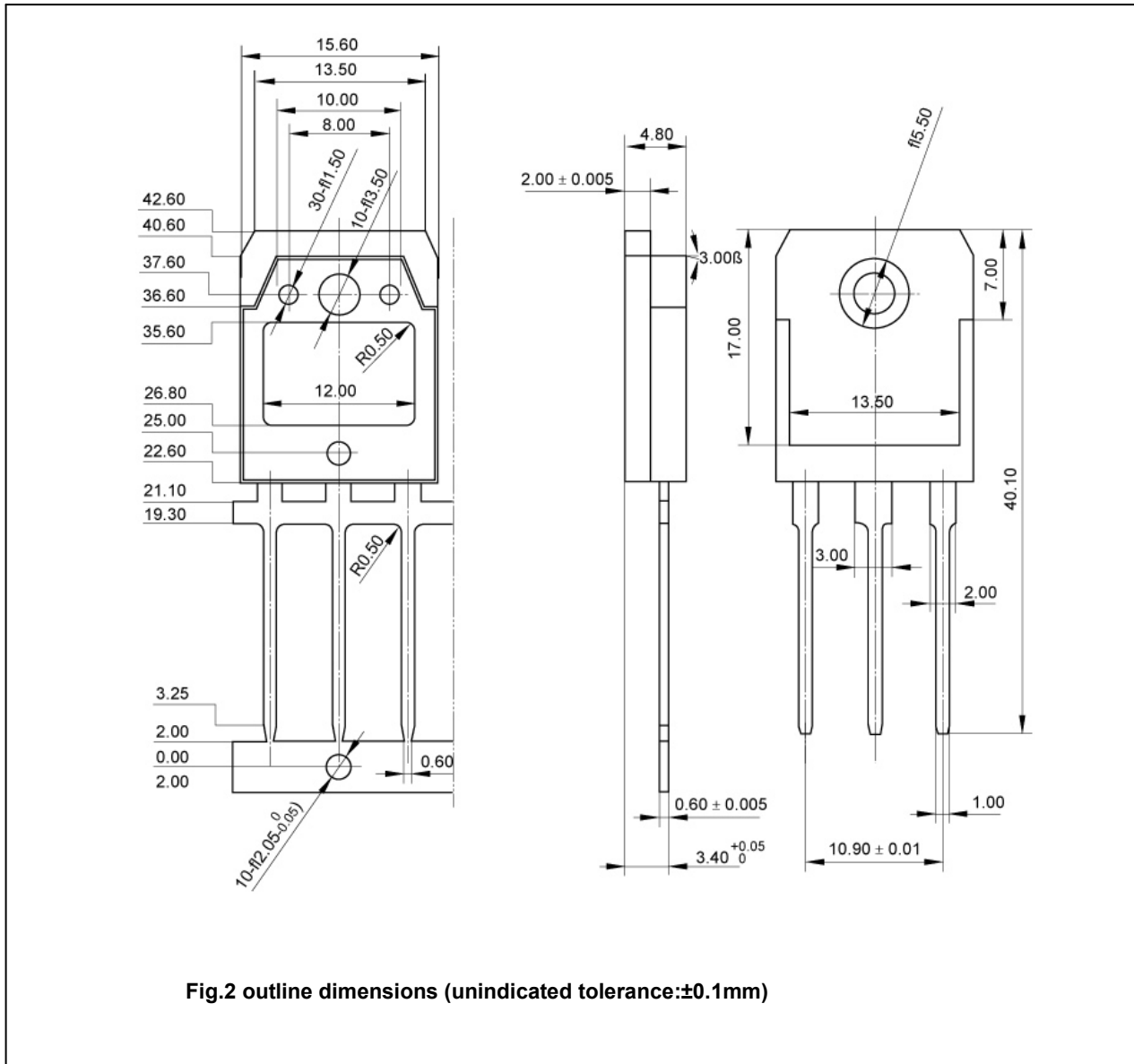


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)

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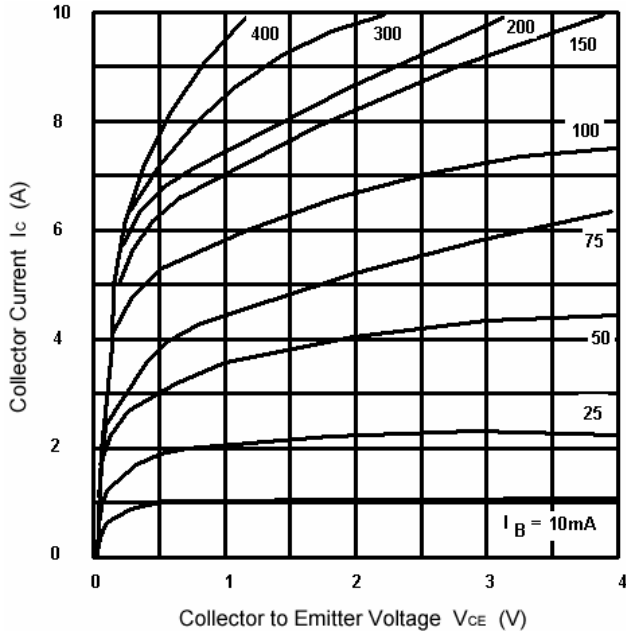


Fig.3 Static Characteristic

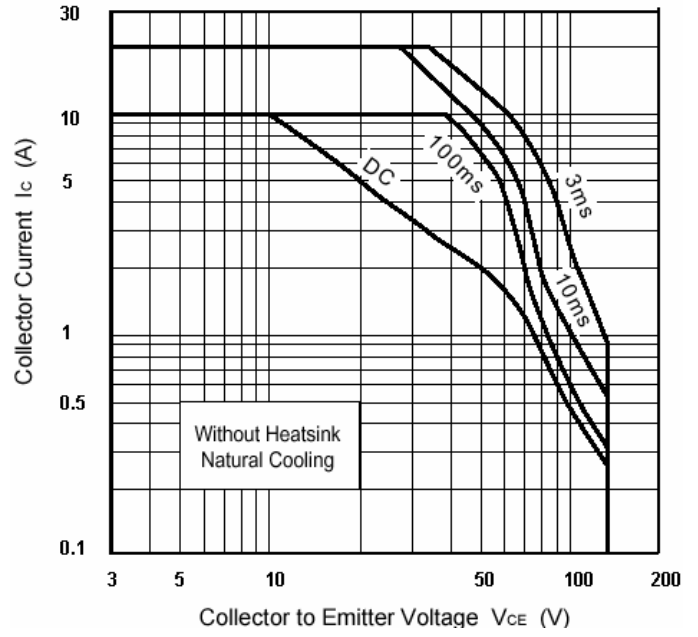


Fig.4 Safe Operating Area

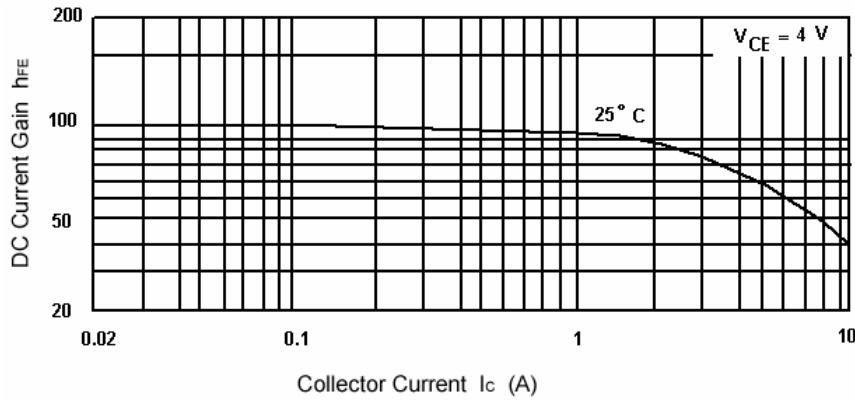


Fig.5 DC current Gain